

ABSTRACT OF THE DISCLOSURE

To avoid that IGBTs are destroyed by receiving overvoltages while an overcurrent flows through series-connected IGBTs of a semiconductor power converting apparatus, a gate driver for controlling a gate voltage of the MOS control semiconductor owns a power supply line having a higher potential than such a gate potential when the MOS control semiconductor is brought into a steady ON state, and when a potential difference between the power supply line and an emitter of the MOS control semiconductor is constant, and also a collector voltage of the MOS control semiconductor exceeds a predetermined value under ON state of the MOS control semiconductor, the power source line of the gate driver supplies a current from the power source line to the gate of the MOS control semiconductor so as to increase the gate voltage of the MOS control semiconductor.